

MITSUBISHI IGBT MODULES
CM400HU-24H
 HIGH POWER SWITCHING USE
 INSULATED TYPE

CM400HU-24H



- Ic 400A
- VCES 1200V
- Insulated Type
- 1-element in a pack
- UL Recognized

Yellow Card No. E80276
 File No. E80271

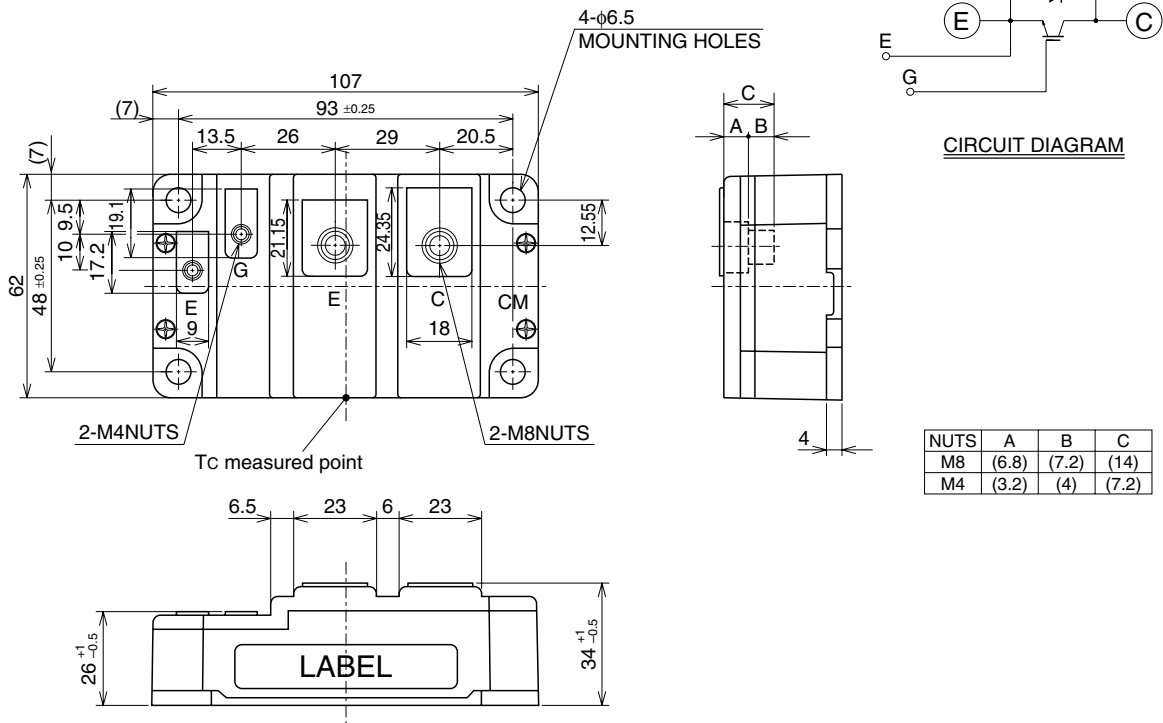
APPLICATION

UPS, NC machine, AC-Drive control, Servo, Welders

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm

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MAXIMUM RATINGS (T_j = 25°C, unless otherwise specified.)

Symbol	Item	Conditions	Ratings	Unit
V _{CEs}	Collector-emitter voltage	V _{GE} = 0V	1200	V
V _{GES}	Gate-emitter voltage	V _{CE} = 0V	±20	V
I _c	Collector current	T _c = 25°C	400	A
I _{CM}		Pulse (Note 1)	800	A
I _E (Note 2)	Emitter current	T _c = 25°C	400	A
I _{EM} (Note 2)		Pulse (Note 1)	800	A
P _C (Note 3)	Maximum collector dissipation	T _c = 25°C	2100	W
T _j	Junction temperature	—	-40 ~ +150	°C
T _{stg}	Storage temperature	—	-40 ~ +125	°C
V _{iso}	Isolation voltage	Charged part to base plate, rms, sinusoidal, AC 60Hz 1min.	2500	V
—	Mounting torque	Main terminals screw M8	8.8 ~ 10.8	N·m
		Mounting screw M6	3.5 ~ 4.5	N·m
		Auxiliary terminals screw M4	1.3 ~ 1.7	N·m
—	Weight	Typical value	450	g

ELECTRICAL CHARACTERISTICS (T_j = 25°C, unless otherwise specified.)

Symbol	Item	Test Conditions	Limits			Unit
			Min	Typ	Max	
I _{CEs}	Collector cutoff current	V _{CE} = V _{CEs} , V _{GE} = 0V	—	—	2	mA
V _{GE(th)}	Gate-emitter threshold voltage	I _c = 40mA, V _{CE} = 10V	4.5	6	7.5	V
I _{GES}	Gate-leakage current	V _{GE} = V _{CEs} , V _{CE} = 0V	—	—	0.5	μA
V _{CE(sat)}	Collector-emitter saturation voltage	T _j = 25°C, I _c = 400A, V _{GE} = 15V (Note 4)	—	3.9	3.7	V
C _{ies}	Input capacitance	T _j = 125°C, V _{CE} = 10V, V _{GE} = 0V	—	6.35	—	nF
C _{oes}	Output capacitance	V _{CE} = 10V, V _{GE} = 0V	—	—	21	nF
C _{res}	Reverse transfer capacitance	V _{CE} = 10V, V _{GE} = 0V	—	—	12	nF
Q _G	Total gate charge	V _{CC} = 600V, I _c = 400A, V _{GE} = 15V	—	1500	—	nC
t _{d(on)}	Turn-on delay time	V _{CC} = 600V, I _c = 400A	—	—	250	ns
t _r	Turn-on rise time	V _{GE1} = V _{GE2} = 15V	—	—	350	ns
t _{d(off)}	Turn-off delay time	R _G = 0.78Ω	—	—	350	ns
t _f	Turn-off fall time	Resistive load switching operation	—	—	350	ns
V _{EC} (Note 2)	Emitter-collector voltage	I _E = 400A, V _{GE} = 0V	—	—	3.2	V
t _{rr} (Note 2)	Reverse recovery time	I _E = 400A, die / dt = -800A / μs	—	—	300	ns
Q _{rr} (Note 2)	Reverse recovery charge	die / dt = -800A / μs	—	2.2	—	μC
R _{th(j-c)Q}	Thermal resistance (Note 5)	Junction to case, IGBT part	—	—	0.06	°C/W
R _{th(j-c)R}		Junction to case, FWDi part	—	—	0.09	°C/W
R _{th(c-f)}	Contact thermal resistance	Case to fin, Thermal grease applied (Note 6)	—	0.02	—	°C/W

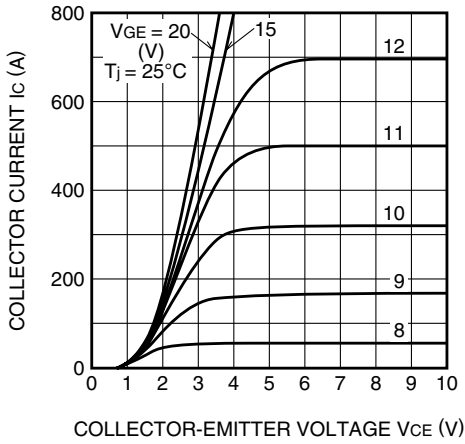
- Note 1. Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed T_{jmax} rating.
 2. I_E, I_{EM}, V_{EC}, t_{rr}, Q_{rr} & die/dt represent characteristics of the anti-parallel, emitter to collector free-wheel diode.
 3. Junction temperature (T_j) should not increase beyond 150°C.
 4. Pulse width and repetition rate should be such as to cause negligible temperature rise.
 5. T_c measured point is shown in page OUTLINE DRAWING.
 6. Typical value is measured by using Shin-Etsu Chemical Co., Ltd. "G-746".

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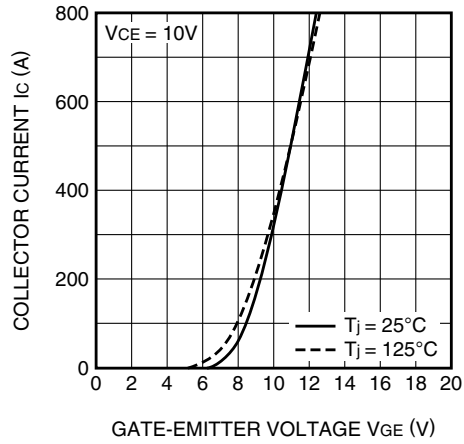
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

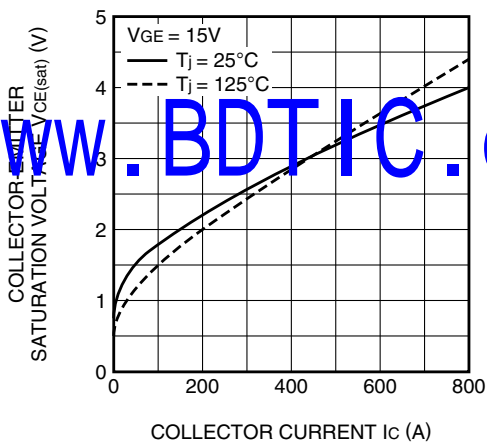
OUTPUT CHARACTERISTICS
(TYPICAL)



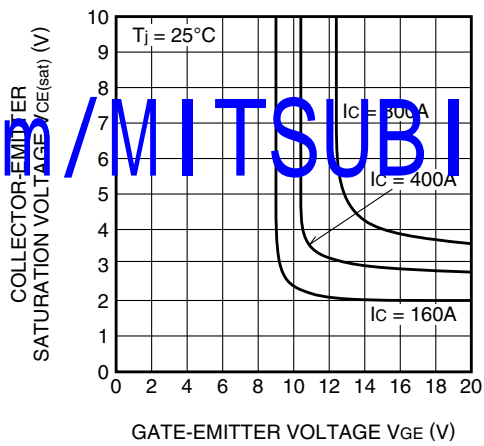
TRANSFER CHARACTERISTICS
(TYPICAL)



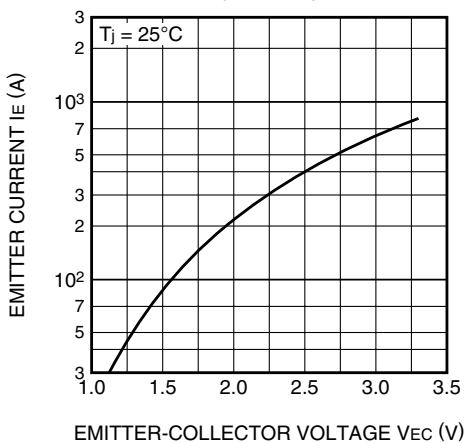
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



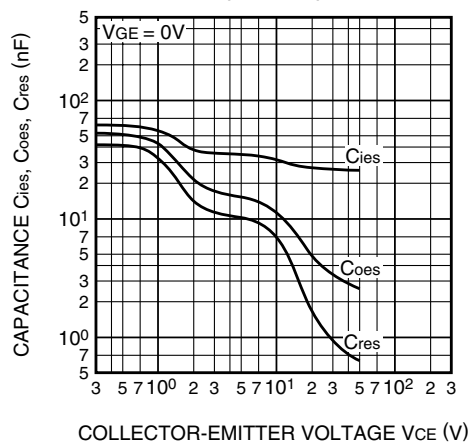
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



CAPACITANCE CHARACTERISTICS
(TYPICAL)

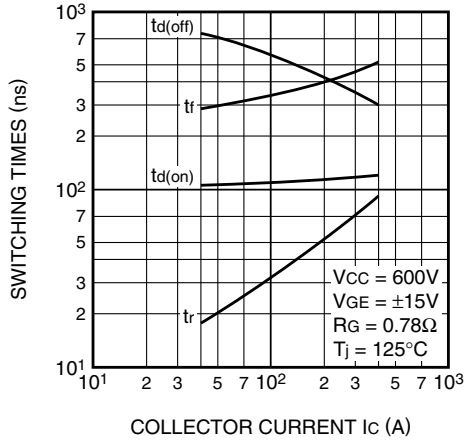


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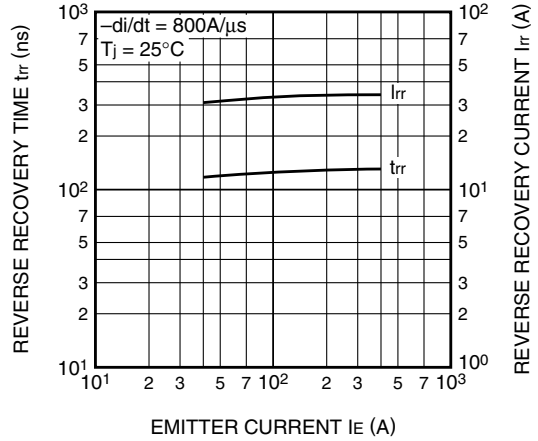
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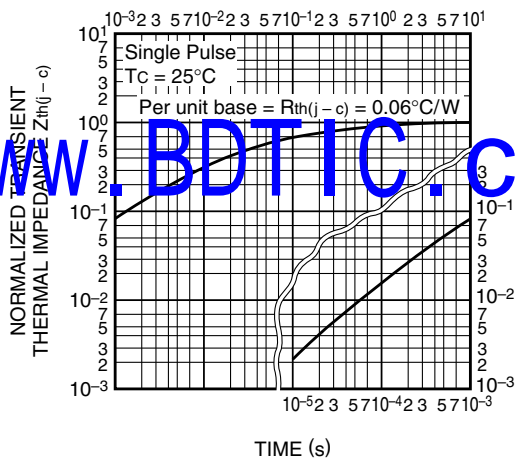
HALF-BRIDGE
SWITCHING TIME CHARACTERISTICS
(TYPICAL)



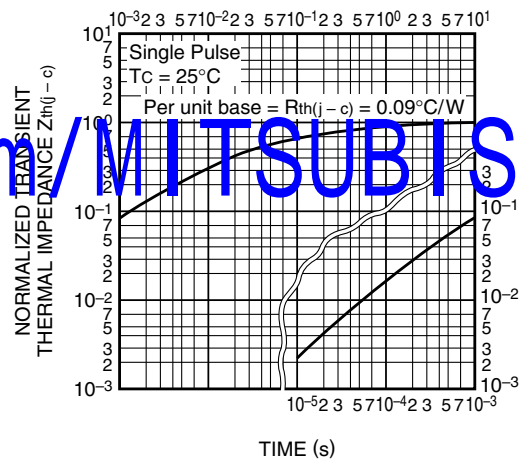
REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)



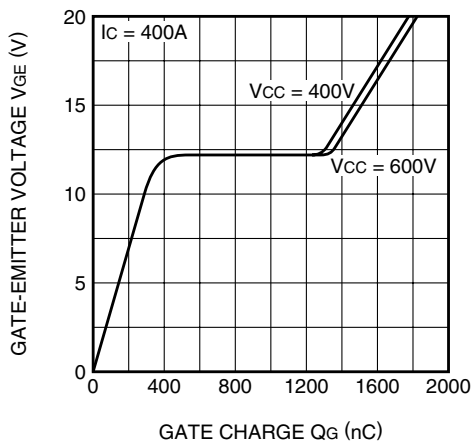
TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT part)



TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(FWDi part)



GATE CHARGE CHARACTERISTICS
(TYPICAL)



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